



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



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Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C (Silicon Limited)	I _D T _C = +25°C (Package Limited)
60V	3.4mΩ @ V _{GS} = 10V	163A	100A

Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} – Minimizes Power Losses
- Low Q_g – Minimizes Switching Losses

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

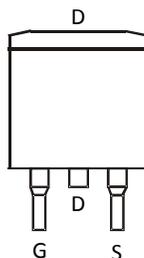
Mechanical Data

- Case: TO263AB (D2PAK)
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 1.7 grams (Approximate)

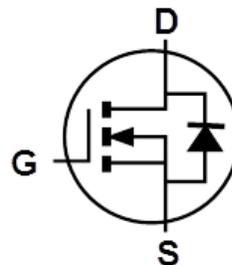


Top View

TO263AB (D2PAK)



Pin Out Top View



Internal Schematic

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current (Silicon Limited, Note 7)	I_D	$T_C = +25^\circ\text{C}$	163
		$T_C = +100^\circ\text{C}$	115
Continuous Drain Current (Package Limited, Note 7)	I_D	$T_C = +25^\circ\text{C}$	100
		$T_C = +100^\circ\text{C}$	100
Maximum Continuous Body Diode Forward Current (Note 7)	I_S	100	A
Pulsed Drain Current (10 μs Pulse, $T_C = +25^\circ\text{C}$, Package Limited)	I_{DM}	400	A
Pulsed Body Diode Forward Current (10 μs Pulse, $T_C = +25^\circ\text{C}$, Package Limited)	I_{SM}	400	A
Avalanche Current, $L=0.2\text{mH}$	I_{AS}	45	A
Avalanche Energy, $L=0.2\text{mH}$	E_{AS}	200	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P_D	4.7	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	32	$^\circ\text{C/W}$
Total Power Dissipation (Note 7)	P_D	136	W
Thermal Resistance, Junction to Case (Note 7)	$R_{\theta JC}$	1.1	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$V_{GS} = 0V, I_D = 1\text{mA}$
Zero Gate Voltage Drain Current (Note 9)	I_{DSS}	—	—	1	μA	$V_{DS} = 48V, V_{GS} = 0V$
		—	—	100	μA	$V_{DS} = 48V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	2	—	4	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	2.9	3.4	m Ω	$V_{GS} = 10V, I_D = 100\text{A}$
Diode Forward Voltage	V_{SD}	—	—	1.3	V	$V_{GS} = 0V, I_S = 100\text{A}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	4,556	—	pF	$V_{DS} = 30V, V_{GS} = 0V$ $f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	1,383	—		
Reverse Transfer Capacitance	C_{rss}	—	105.2	—		
Gate Resistance	R_g	0.1	0.66	1.9	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1\text{MHz}$
Total Gate Charge	Q_g	—	95.4	—	nC	$V_{DD} = 30V, I_D = 90\text{A},$ $V_{GS} = 10V$
Gate-Source Charge	Q_{gs}	—	21.6	—		
Gate-Drain Charge	Q_{gd}	—	20.4	—		
Turn-On Delay Time	$t_{D(ON)}$	—	13.2	—	ns	$V_{DD} = 30V, V_{GS} = 10V,$ $I_D = 90\text{A}, R_g = 3.5\Omega$
Turn-On Rise Time	t_r	—	11.7	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	31	—		
Turn-Off Fall Time	t_f	—	12	—		
Reverse Recovery Time	t_{RR}	—	50.5	—	ns	$I_F = 50\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge	Q_{RR}	—	80.8	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

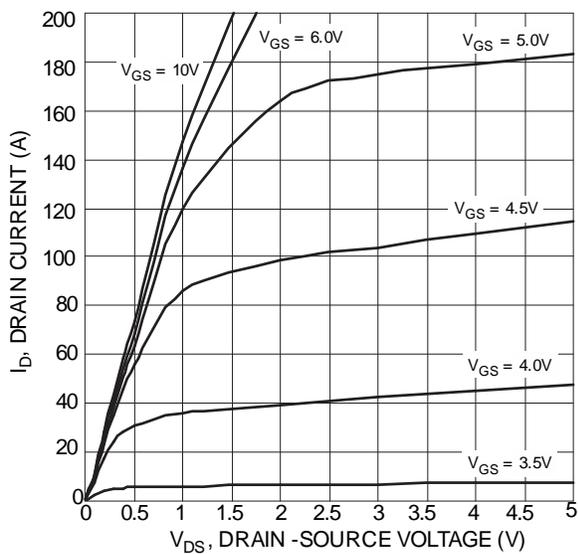


Figure 1 Typical Output Characteristics

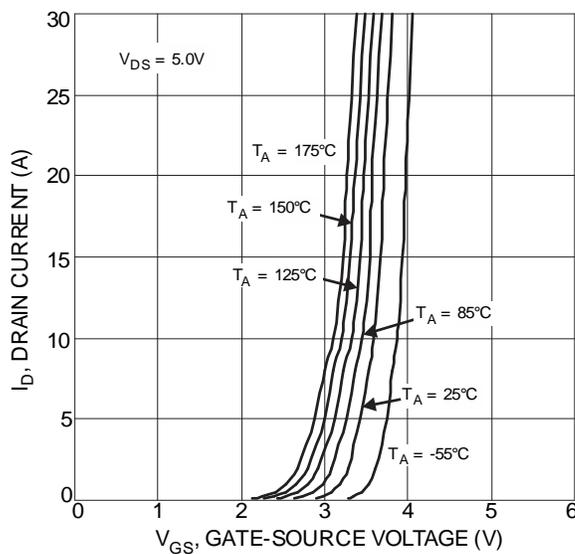


Figure 2 Typical Transfer Characteristics

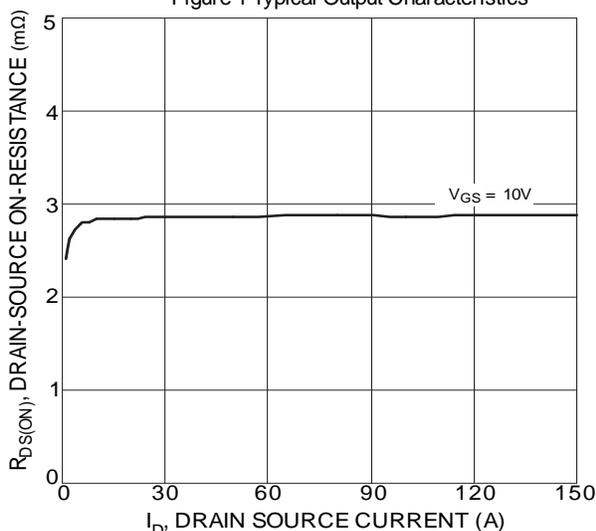


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

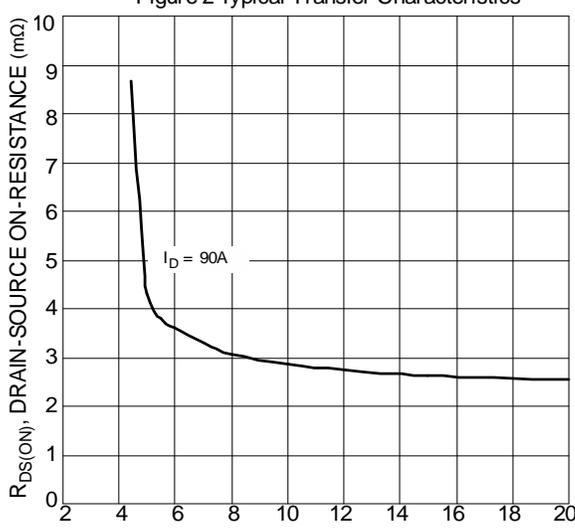


Figure 4 Typical Transfer Characteristic

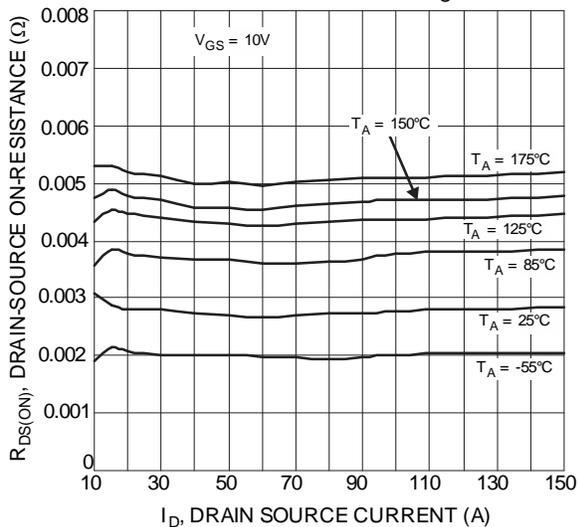


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

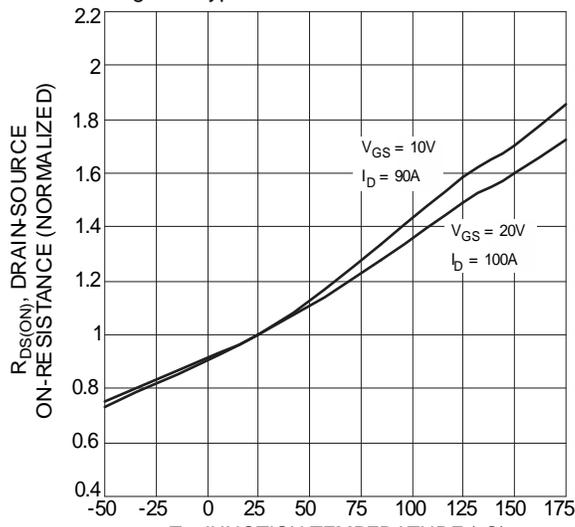


Figure 6 On-Resistance Variation with Temperature

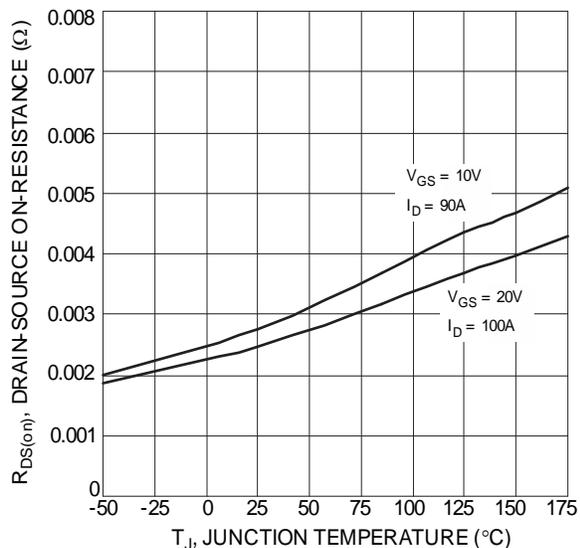


Figure 7 On-Resistance Variation with Temperature

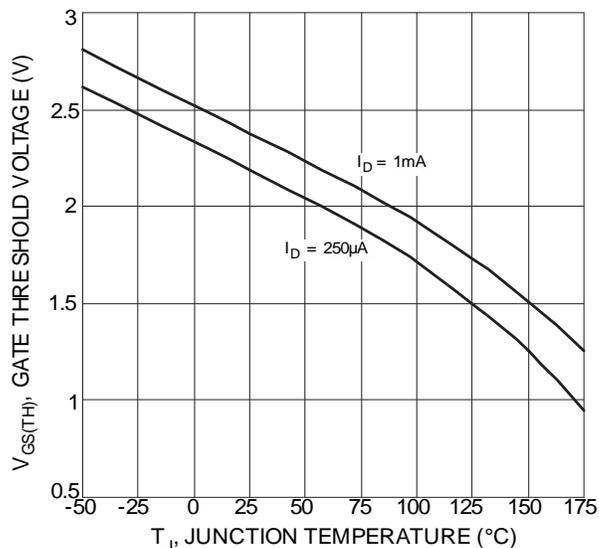


Figure 8 Gate Threshold Variation vs. Temperature

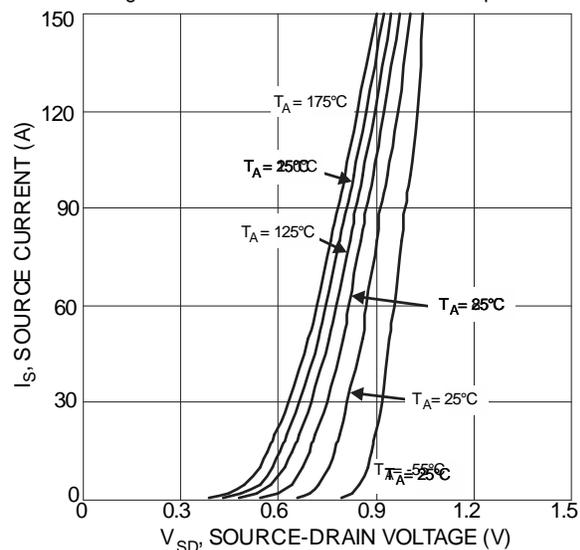


Figure 9 Diode Forward Voltage vs. Current

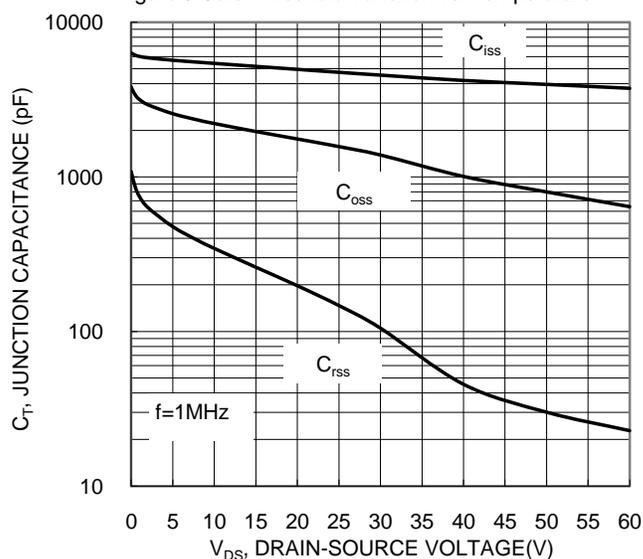


Figure 10. Typical Junction Capacitance

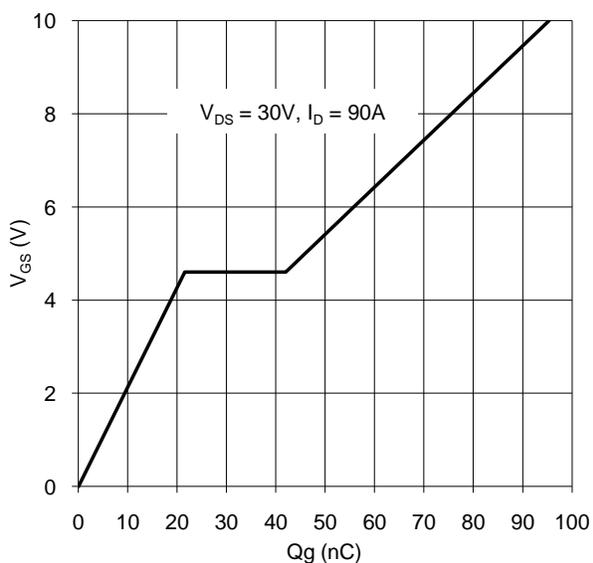


Figure 11. Gate Charge

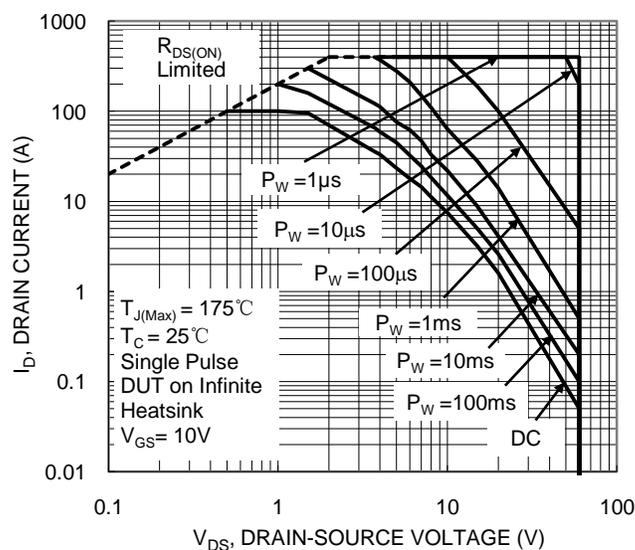


Figure 12. SOA, Safe Operation Area

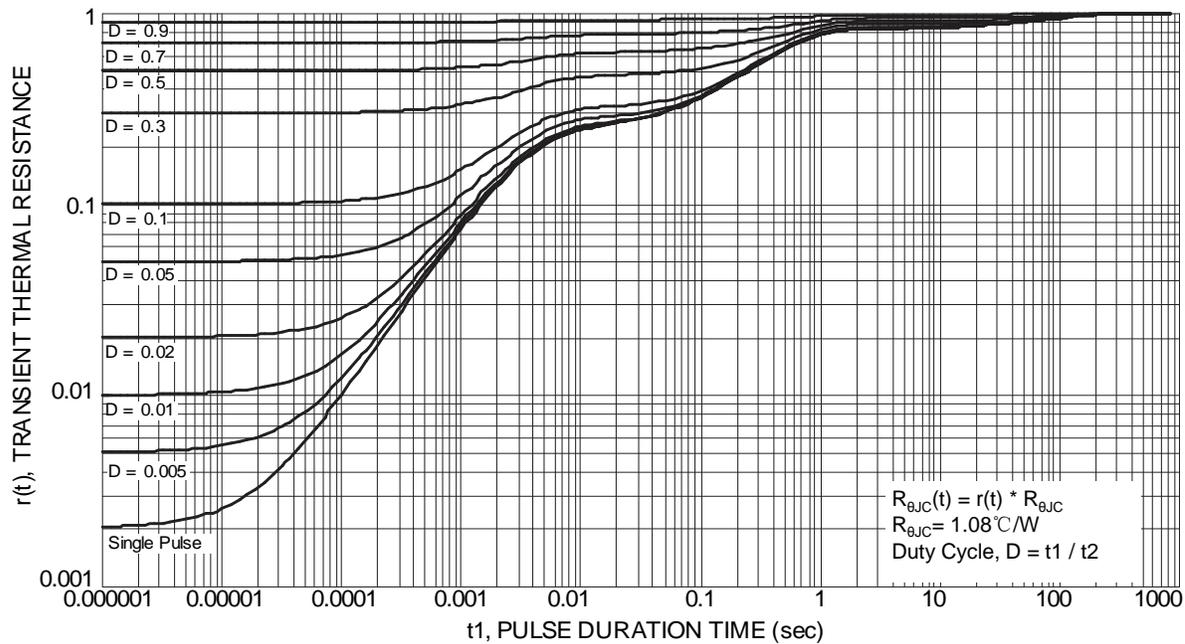
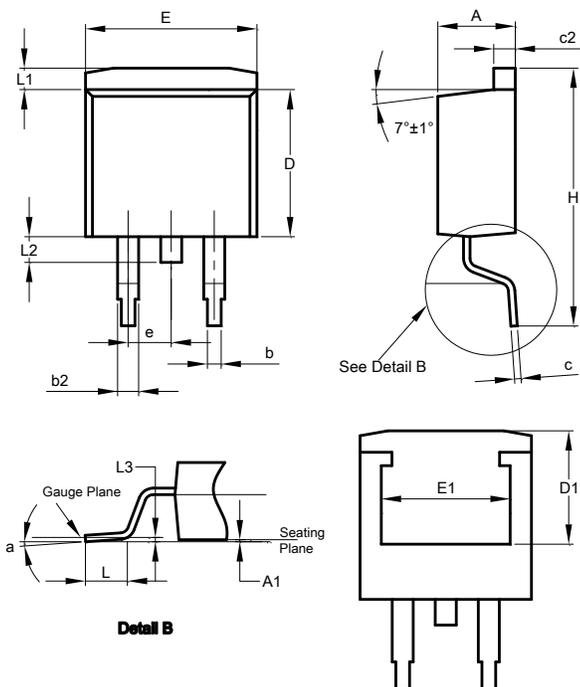


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

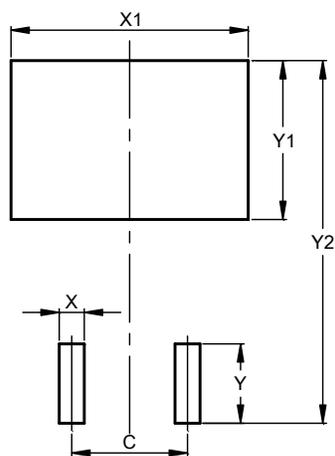
TO263AB (D2PAK)



TO263AB (D2PAK)			
Dim	Min	Max	Typ
A	4.07	4.82	-
A1	0.00	0.25	-
b	0.51	0.99	-
b2	1.15	1.77	-
c	0.356	0.73	-
c2	1.143	1.65	-
D	8.39	9.65	-
D1	6.55	6.95	-
e	2.54 TYP		
E	9.66	10.66	-
E1	6.23	8.23	-
H	14.61	15.87	-
L	1.78	2.79	-
L1	-	1.67	-
L2	-	1.77	-
L3	-	-	0.254
a	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

TO263AB (D2PAK)



Dimensions	Value (in mm)
C	5.08
X	1.10
X1	10.41
Y	3.50
Y1	7.01
Y2	15.99